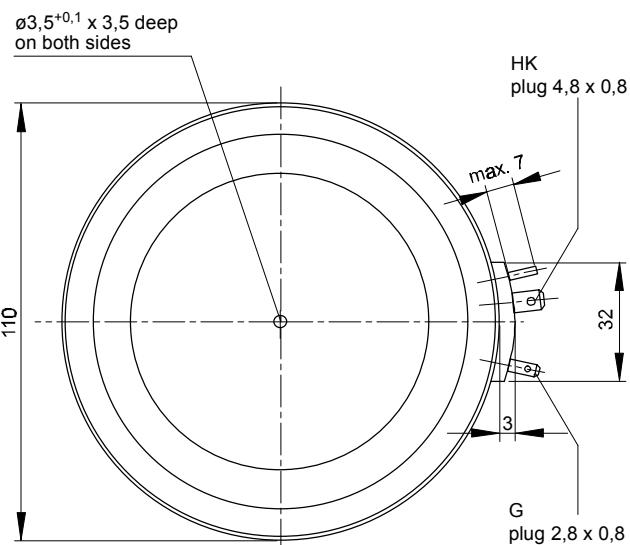
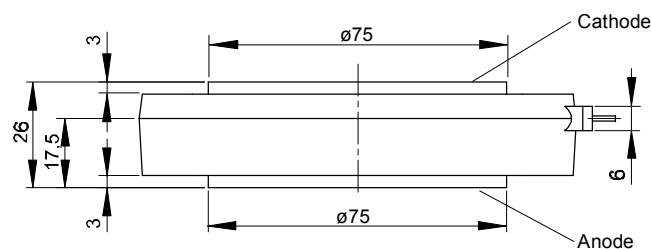




European Power-
Semiconductor and
Electronics Company

Marketing Information T 1549 N



T 1549 N 30...38

Elektrische Eigenschaften

Höchstzulässige Werte

Periodische Vorwärts- und Rückwärts-Spitzenspannung
Vorwärts-Stoßspitzenperrspannung

Rückwärts-Stoßspitzenperrspannung

Durchlaßstrom-Grenzeffektivwert

Dauergrenzstrom

Stoßstrom-Grenzwert

Grenzlastintegral

Kritische Stromteilheit

Kritische Spannungsteilheit

Electrical properties

Maximum rated values

repetitive peak forward off-state and reverse voltage

non-repetitive peak forward off-state voltage

non-repetitive peak reverse voltage

RMS on-state current

average on-state current

surge current

$I^2 t$ -value

critical rate of rise of on-state current

critical rate of rise of off-state voltage

$t_{vj} = -40^\circ C \dots t_{vj \max}$

$t_{vj} = -40^\circ C \dots t_{vj \max}$

$t_{vj} = +25^\circ C \dots t_{vj \max}$

$t_c = 85^\circ C$

$t_c = 49^\circ C$

$t_{vj} = 25^\circ C, t_p = 10 \text{ ms}$

$t_{vj} = t_{vj \max}, t_p = 10 \text{ ms}$

$t_{vj} = 25^\circ C, t_p = 10 \text{ ms}$

$t_{vj} = t_{vj \max}, t_p = 10 \text{ ms}$

DIN IEC 747-6, $f = 50 \text{ Hz}$,

$v_L = 10 \text{ V}, i_{GM} = 1,6 \text{ A}, di_G/dt = 1,6 \text{ A}/\mu\text{s}$

$t_{vj} = t_{vj \max}, v_D = 0,67 V_{DRM}$

5.Kennbuchstabe/5th letter C

5.Kennbuchstabe/5th letter F

V_{DRM}, V_{RRM}

3000 3200 3400 V¹⁾

3600 3800

V_{DSM}

3000 3200 3400 V

3600 3800

V_{RSM}

3100 3300 3500 V

3700 3900

I_{TRMSM}

3800 A

I_{TAVM}

1575 A

I_{TSM}

2420 A

$I^2 t$

6125 · 10³ A²s

$(di_T/dt)_{cr}$

4805 · 10³ A²s

$(dv_D/dt)_{cr}$

150 A/ μ s

$500 \text{ V}/\mu\text{s}$

$1000 \text{ V}/\mu\text{s}$

Charakteristische Werte

Durchlaßspannung

Schleusenspannung

Ersatzwiderstand

Zündstrom

Zündspannung

Nicht zündender Steuerstrom

Nicht zündende Steuerspannung

Haltestrom

Einraststrom

Vorwärts- und Rückwärts-Sperrstrom

Zündverzug

Freiwerdezeit

Characteristic values

on-state voltage

threshold voltage

slope resistance

gate trigger current

gate trigger voltage

gate non-trigger current

gate non-trigger voltage

holding current

latching current

forward off-state and reverse currents

gate controlled delay time

circuit commutated turn-off time

$t_{vj} = t_{vj \max}, i_T = 7250 \text{ A}$

$t_{vj} = t_{vj \max}$

$t_{vj} = t_{vj \max}$

$t_{vj} = 25^\circ C, v_D = 6 \text{ V}$

$t_{vj} = 25^\circ C, v_D = 6 \text{ V}$

$t_{vj} = t_{vj \max}, v_D = 6 \text{ V}$

$t_{vj} = t_{vj \max}, v_D = 0,5 V_{DRM}$

$t_{vj} = t_{vj \max}, v_D = 0,5 V_{DRM}$

$t_{vj} = 25^\circ C, v_D = 6 \text{ V}, R_A = 5 \Omega$

$t_{vj} = 25^\circ C, v_D = 6 \text{ V}, R_{GK} \geq 10 \Omega$

$i_{GM} = 1,6 \text{ A}, di_G/dt = 1,6 \text{ A}/\mu\text{s}, t_g = 20 \mu\text{s}$

$t_{vj} = t_{vj \max}, V_D = V_{DRM}, V_R = V_{RRM}$

DIN IEC 747-6, $t_{vj}=25^\circ C, i_{GM}=1,6A, t_{gd}=1,6A/\mu s$

$t_{vj} = t_{vj \max}, i_{TM} = i_{TAVM}, v_{RM} = 100 \text{ V}, v_{DM} = 0,67 t_q$

$v_{DRM}, dv_D/dt = 20 \text{ V}/\mu\text{s}, -di_T/dt = 10 \text{ A}/\mu\text{s},$

4 Kennbuchstabe/4th letter Ω

v_T

max. 3,78 V

$V_{T(TO)}$

1,40 V

r_T

0,30 mΩ

I_{GT}

max. 300 mA

V_{GT}

max. 3 V

I_{GD}

max. 10 mA

V_{GD}

max. 5 mA

i_D, i_R

max. 400 mA

t_{gd}

max. 3 μs

t_q

typ. 200 μs

Thermische Eigenschaften

Innerer Wärmewiderstand

Thermal properties

thermal resistance, junction to case

Kühlfläche/cooling surface

R_{thJC}

max. 0,0099 °C/W

Übergangs-Wärmewiderstand

thermal resistance, case to heatsink

Kühlfläche/cooling surface

R_{thCK}

max. 0,0092 °C/W

Höchstzul. Sperrsichttemperatur

max. junction temperature

$t_{vj \max}$

125 °C

Betriebstemperatur

operating temperature

t_c_{op}

-40...+125 °C

Lagertemperatur

storage temperature

t_{stg}

-40...+150 °C

Mechanische Eigenschaften

Mechanical properties

Si-Elemente mit Druckkontakt, Amplifying-

Si-pellet with pressure contact, amplifying

Gate verzweigt

gate interdigitated

Anpreßkraft

clamping force

F

42...95 kN

Gewicht

weight

G

typ. 1200 g

Kriechstrecke

creepage distance

30 mm

Feuchtekategorie

humidity classification

DIN 40040

C

Schwingfestigkeit

vibration resistance

f = 50 Hz

50 m/s²

Gehäuse

case

Titelseite / front page

¹⁾ 3800 V auf Anfrage / 3800 V on demand

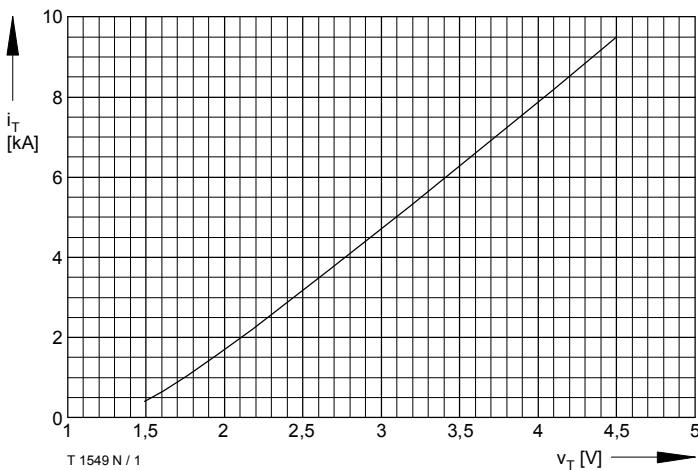


Bild / Fig. 1
Grenzdurchlaßkennlinie / Limiting on-state characteristic $i_T = f(v_T)$
 $t_{vj} = t_{vj \max}$

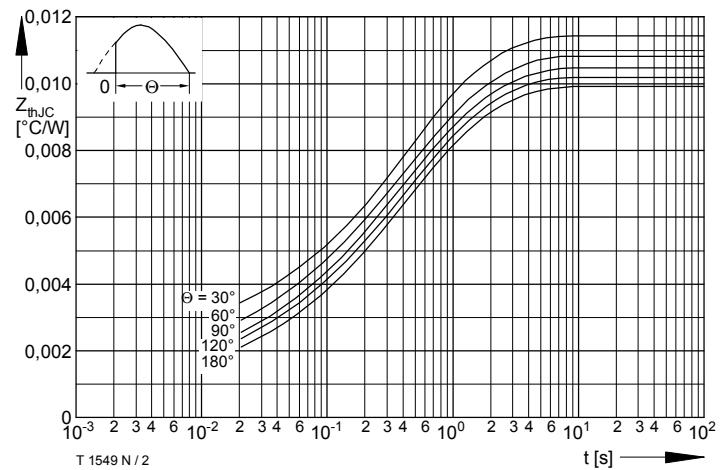


Bild / Fig. 2
Transienter innerer Wärmewiderstand / Transient thermal impedance
 $Z_{thJC} = f(t)$
Beidseitige Kühlung / Two-sided cooling
Parameter: Stromflußwinkel / Current conduction angle θ

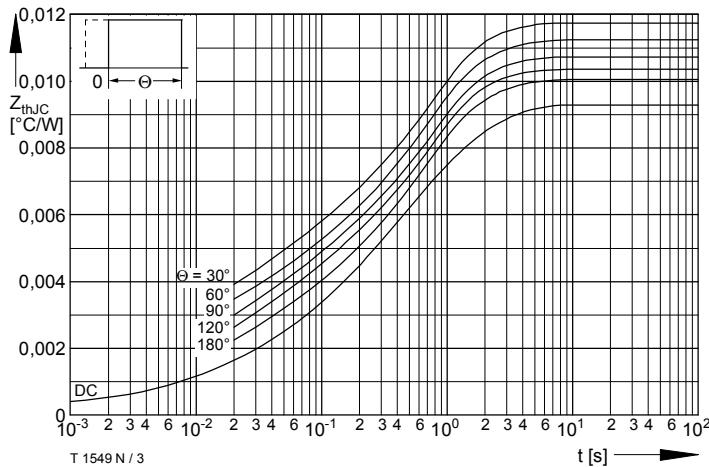


Bild / Fig. 3
Transienter innerer Wärmewiderstand / Transient thermal impedance
 $Z_{thJC} = f(t)$
Beidseitige Kühlung / Two-sided cooling
Parameter: Stromflußwinkel / Current conduction angle θ

Analytische Elemente des transienten Wärmewiderstandes Z_{thJC} pro Zweig für DC
Analytical elements of transient thermal impedance Z_{thJC} per arm for DC

Beidseitig / Two-sided

Pos. n	1	2	3	4	5	6
R_{thn} [°C/W]	0,00003	0,00039	0,00123	0,00317	0,00438	
τ_n [s]	0,000055	0,00392	0,0152	0,2068	1,0914	

Analytische Funktion / Analytical function:

$$Z_{thJC} = \sum_{n=1}^{n_{\max}} R_{thn} (1 - e^{-\frac{t}{\tau_n}})$$